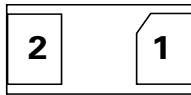


**SP1054 25pF 30kV 01005 DFN Plastic Unidirectional Discrete TVS** HF RoHS Pb GREEN



**Pinout**



Note: Drawing not to scale

**Functional Block Diagram**



**Description**

Avalanche breakdown diodes fabricated in a proprietary silicon avalanche technology protect each I/O pin to provide a high level of protection for electronic equipment that may experience destructive electrostatic discharges (ESD). These robust diodes can safely absorb repetitive ESD strikes at  $\pm 30\text{kV}$  (contact discharge, IEC 61000-4-2) without performance degradation. Additionally, each diode can safely withstand 2.5A surge (8/20 waveshape as defined in IEC 61000-4-5 2<sup>nd</sup> edition) at a very low clamping voltage.

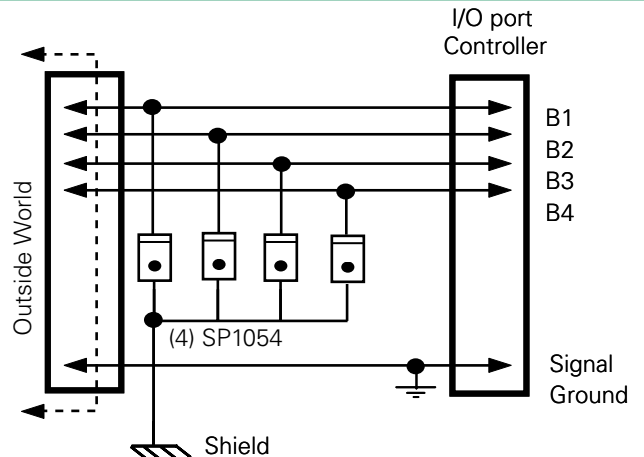
**Features**

- ESD, IEC 61000-4-2,  $\pm 30\text{kV}$  contact,  $\pm 30\text{kV}$  air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 2.5A (8/20 as defined in IEC 61000-4-5 2<sup>nd</sup> edition)
- Low capacitance of 25.5 pF (@  $V_R = 0\text{V}$ )
- Low leakage current of  $0.02\mu\text{A}$  (TYP) at 5V
- Unidirectional solutions presents half the dynamic resistance of a bidirectional device protects faster and better
- Industry's smallest ESD footprint available (01005 DFN plastic)
- Moisture Sensitivity Level (MSL -1)
- Halogen free, lead free and RoHS compliant
- AEC-Q101 qualified

**Applications**

- Mobile Phones
- Smart Phones
- Camcorders
- Portable Medical
- Digital Cameras
- Wearable Technology
- Portable Navigation Components
- Tablets
- Point of Sale Terminals
- Identification Modules

**Application Example**



Life Support Note:

**Not Intended for Use in Life Support or Life Saving Applications**

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
$I_{PP}$	Peak Current ( $t_p=8/20\mu s$ )	2.5 <sup>1</sup>	A
$T_{OP}$	Operating Temperature	-40 to 125	°C
$T_{STOR}$	Storage Temperature	-55 to 150	°C

Notes:

1. CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### Electrical Characteristics ( $T_{OP}=25^\circ C$ )

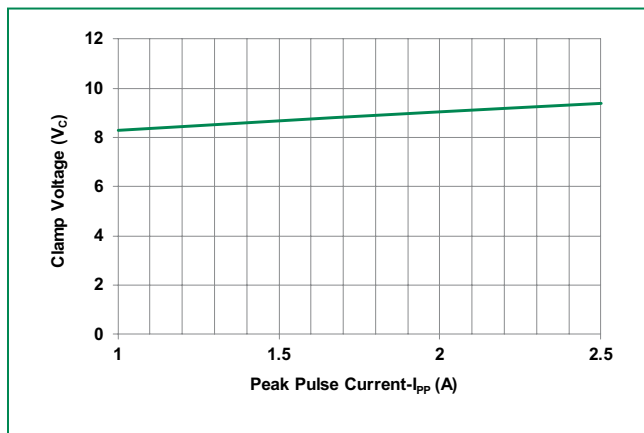
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	$V_{RWM}$	$I_R \leq 1\mu A$			6.0	V
Breakdown Voltage	$V_{BR}$	$I_R = 1mA$	6.5	7.2		V
Leakage Current	$I_{LEAK}$	$V_R = 5V$ with 1 pin at GND		0.02	0.5	$\mu A$
Clamp Voltage <sup>1</sup>	$V_C$	$I_{PP} = 1A, t_p = 8/20\mu s, Fwd$		8.5	11	V
		$I_{PP} = 2A, t_p = 8/20\mu s, Fwd$		9.5	13	V
Dynamic Resistance <sup>2</sup>	$R_{DYN}$	TLP, $t_p = 100ns, I/O$ to GND		0.21		$\Omega$
ESD Withstand Voltage <sup>1</sup>	$V_{ESD}$	IEC 61000-4-2 (Contact Discharge)	$\pm 30$			kV
		IEC 61000-4-2 (Air Discharge)	$\pm 30$			kV
Diode Capacitance <sup>1</sup>	$C_D$	Reverse Bias=0V		26		pF

Note:

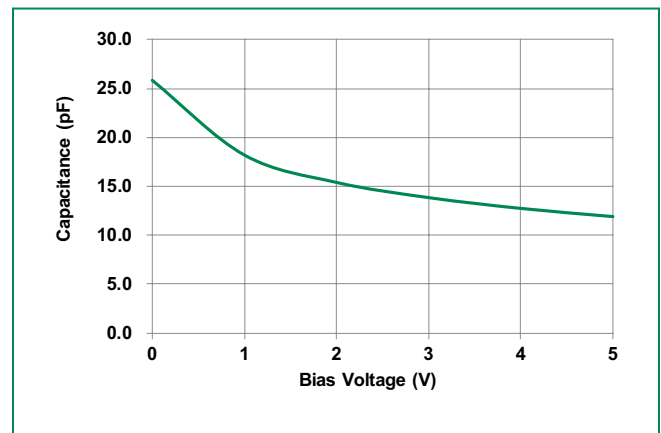
1 Parameter is guaranteed by design and/or component characterization.

2 Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window  $t_1=70ns$  to  $t_2=90ns$

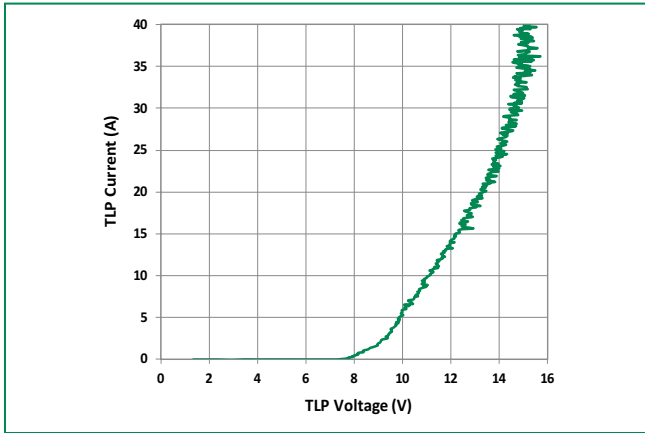
### Clamping voltage vs. $I_{PP}$ for 8/20 $\mu s$ Waveshape



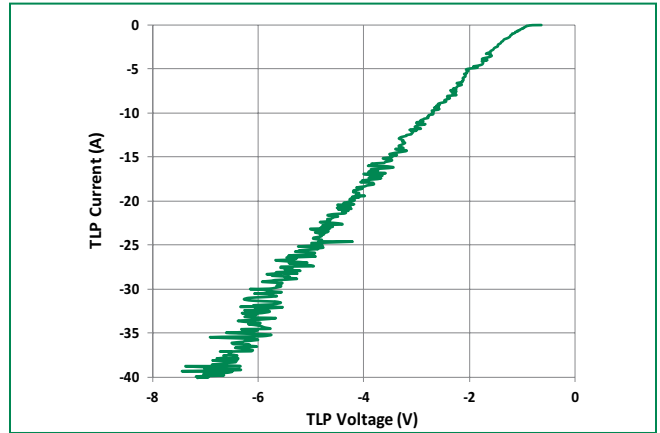
### Capacitance vs. Bias



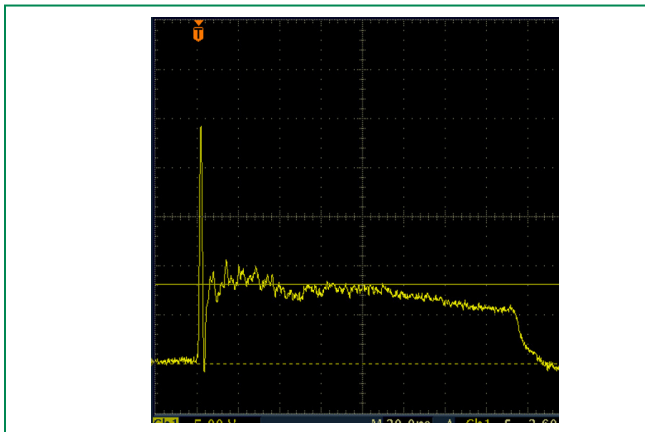
**Positive Transmission Line Pulsing (TLP) Plot**



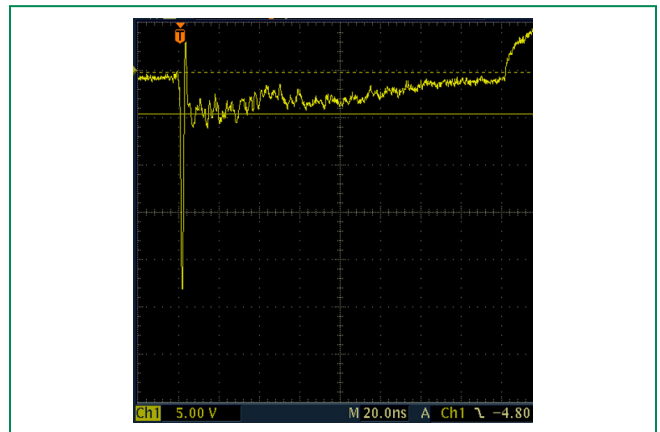
**Negative Transmission Line Pulsing (TLP) Plot**



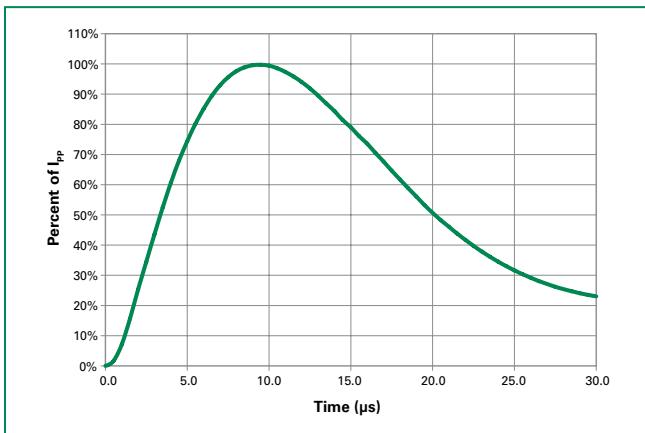
**IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage**



**IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage**

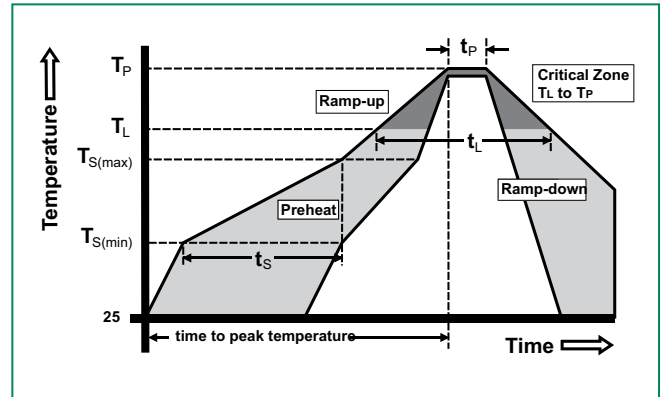


**8/20µs Pulse Waveform**



### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus) Temp ( $T_L$ ) to peak		3°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		260°C



### Part Marking System



### Ordering Information

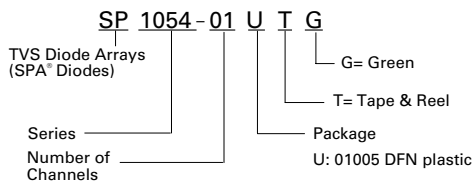
Part Number	Package	Min. Order Qty.
SP1054-01UTG	01005 DFN plastic	20000

### Product Characteristics

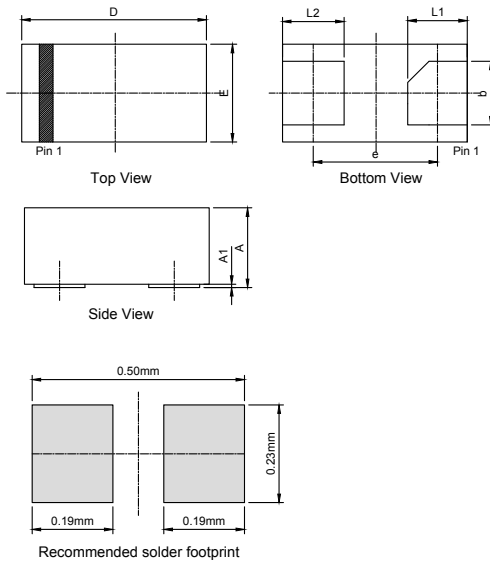
<b>Lead Plating</b>	Pre-Plated Frame
<b>Lead Material</b>	Copper Alloy
<b>Substrate material</b>	Silicon
<b>Body Material</b>	Molded Compound
<b>Flammability</b>	UL Recognized compound meeting flammability rating V-0.

- Notes :
1. All dimensions are in millimeters
  2. Dimensions include solder plating.
  3. Dimensions are exclusive of mold flash & metal burr.

### Part Numbering System

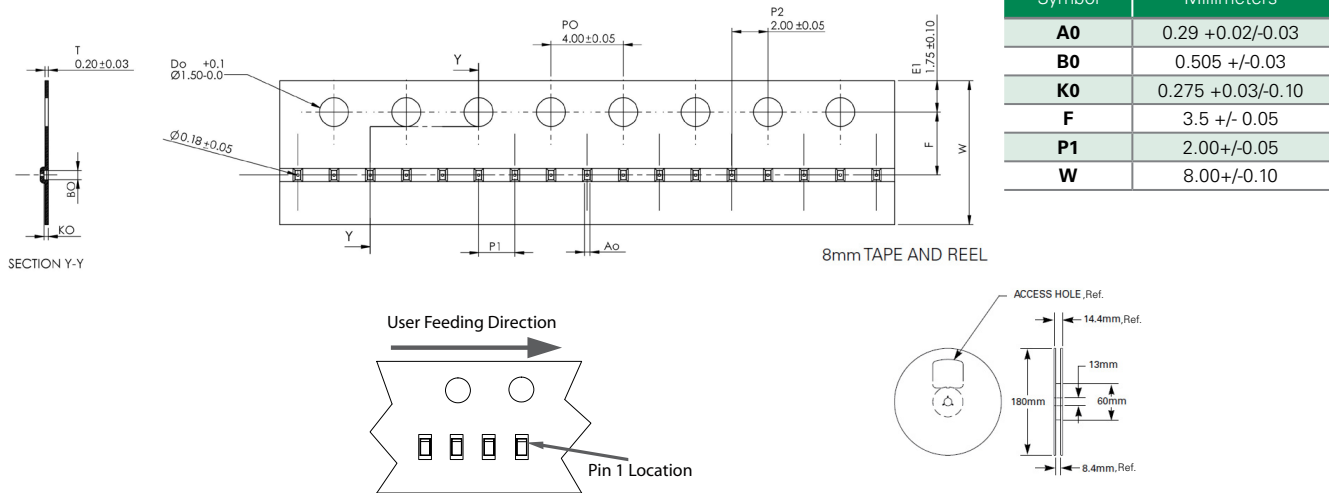


## Package Dimensions — 01005 DFN



Symbol	01005 DFN plastic					
	Millimeters			Inches		
	Min	Typ	Max	Min	Typ	Max
<b>A</b>	0.235	0.250	0.265	0.0093	0.0098	0.0104
<b>A1</b>	-	0.015	0.020	-	0.0006	0.0008
<b>b</b>	0.100	0.150	0.200	0.0039	0.0059	0.0079
<b>D</b>	0.385	0.435	0.485	0.0152	0.0171	0.0191
<b>E</b>	0.200	0.250	0.300	0.0079	0.0098	0.0118
<b>e</b>	0.293			0.0115		
<b>L1</b>	0.090	0.140	0.190	0.0035	0.0055	0.0075
<b>L2</b>	0.095	0.145	0.195	0.0037	0.0057	0.0077

## Embossed Carrier Tape & Reel Specification — 01005 DFN plastic



Symbol	Millimeters
<b>A0</b>	0.29 +0.02/-0.03
<b>B0</b>	0.505 +/-0.03
<b>K0</b>	0.275 +0.03/-0.10
<b>F</b>	3.5 +/- 0.05
<b>P1</b>	2.00+/-0.05
<b>W</b>	8.00+/-0.10

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